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(54) **SEMICONDUCTOR DEVICE AND
OVERCURRENT PROTECTION DEVICE**

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ABSTRACT

A semiconductor device includes an output element configured to switch on and off based on a drive signal, so as to drive a load, a current monitoring element configured to monitor a current that flows through the output element, and a voltage control circuit that includes a first diode configured to charge a gate voltage applied to a gate of the current monitoring element and a second diode configured to discharge the gate voltage, so that the voltage control circuit controls the gate voltage. An anode of the first diode is connected to a gate of the output element and a cathode of the second diode, and a cathode of the first diode is connected to an anode of the second diode and the gate of the current monitoring element.

